What is claimed is:

1. A gas supply assembly for providing a gas mixture comprising germanium tetrafluoride (GeF_4) and hydrogen (H_2) gases in an ion implantation chamber comprising:

one or more fluid supply package(s) comprising GeF_4 and H_2 wherein the assembly is configured to provide a gas mixture comprising GeF_4 and H_2 an ion implantation chamber, wherein H_2 is present in an amount in the range of 25%-67% (volume) of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 3:1 to 33:67.

2. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 37-67% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 63:37 to 33:67.

3. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 42-62% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 29:21 to 19:31

4. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 45-59% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 11:9 to 41:59

5. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 47-57% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 53:47 to 43:57.

6. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 49-55% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 51:49 to 9:11.

7. The gas supply assembly of claim 1 wherein H_2 is present in an amount in the range of 51-53% of the gas mixture, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 49:51 to 47:53.

8. The gas supply assembly of claim 1, wherein the gases consist essentially of GeF_4 and H_2.

9. The gas supply assembly of claim 1, further comprising an inert gas selected from the group consisting of argon, helium, neon, nitrogen, xenon, and krypton.

10. The gas supply assembly of claim 1, wherein GeF_4 and H_2 are mixed in a single fluid supply package.

11. The gas supply assembly of claim 1, wherein GeF_4 is present in a GeF_4-containing gas supply package and H_2 is present in a separate H_2-containing gas supply package.

12. The gas supply assembly of claim 1, wherein GeF_4 is not isotopically enriched.

13. A method of implanting germanium in a substrate, comprising introducing germanium tetrafluoride (GeF_4) and hydrogen (H_2) gases into an ion implantation chamber comprising, wherein introducing provides a gas mixture comprising GeF_4 and H_2 an ion implantation chamber, wherein H_2 is present in an amount in the range of 25%-67%, or GeF_4 and H_2 are present in a volume ratio (GeF_4:H_2) in the range of 3:1 to 33:67.